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Substitute for form 1449A/PTO

JUN 03 2005

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet

1

of

2

Complete if Known

Application Number	10/727,999
Filing Date	Dec 3, 2003
First Named Inventor	Witold P. Maszara
Art Unit	2818
Examiner Name	Mai-Houng C. Tran
Attorney Docket Number	H1855

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
M.H.	1A	US- 4,885,617	12/05/1989	Majure-Espejo et al.	
	1B	US-			
	1C	US-			
	1D	US-			
	1E	US-			
	1F	US-			
	1G	US-			
	1H	US-			
	1I	US-			
	1J	US-			
	1K	US-			

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ "Number" "Kind Code ⁴ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
	2A					
	2B					
	2C					
	2D					
	2E					

Examiner Signature	<i>Mallocon</i>	Date Considered	06/30/05
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*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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Substitute for form 1449B/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet

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Complete if Known	
Application Number	10/727,999
Filing Date	Dec 3, 2003
First Named Inventor	Witold P. Maszara
Art Unit	2818
Examiner Name	Mai-Houng C. Tran
Attorney Docket Number	H1855

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
<i>WHT</i>	3A	Wittner, M., C-Y. Ting, I. Ohdomari, and K. N. Tu, "Redistribution of As during Pd ₂ Si formation: Ion channeling measurements", Journal of Applied Physics, American Institute of Physics. New York, US, vol. 53, no. 10, October 1982 (1982-10). Pages 6781-6786, XPP000828298 ISSN: 0021-8979 page 6781- page 6786; figure 8	
<i>WHT</i>	3B	Sun, Jie J., Jiunn-Yann Tsai, and Carlton M. Osburn, "Elevated N+/P Junctions by Implant Into Cosi2 Formed on Selective Epitaxy for Deep Submicron Mosfet's" IEEE Transactions on Electron Devices, IEEE Inc. New York, US, vol. 45, no. 9, September 1998 (1998-9) pages 1946-1952, XP00078297 ISSN: 0018-9383 abstract; figures 307	
	3C		
	3D		
	3E		
	3F		
	3G		
	3H		
	3I		
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Examiner Signature

Mai-Houng C. Tran

Date Considered

06/30/05

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